



SOT-23 Silicon Epitaxial Planar Switching Diode

1SS184

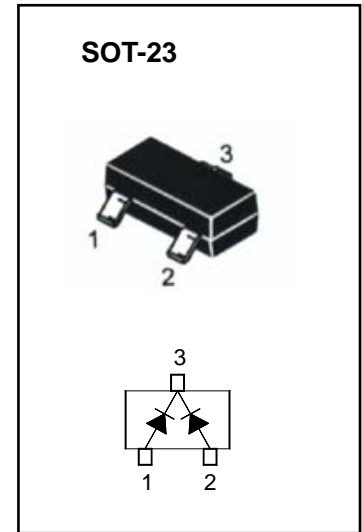
Features

- Small package
- Low forward voltage
- Fast reverse recovery time
- Small total capacitance

Applications

- Ultra high speed switching application

Marking Code: B3



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V _{RM}	85	V
Reverse Voltage	V _R	80	V
Average Rectified Forward Current	I _{F(AV)}	100	mA
Maximum Peak Forward Current	I _{FM}	300	mA
Non-repetitive Peak Forward Surge Current (10 ms)	I _{FSM}	2	A
Power Dissipation	P _{tot}	350	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 100 mA	V _F	1.2	V
Reverse Current at V _R = 30 V at V _R = 80 V	I _R	0.1 0.5	µA
Total Capacitance at V _R = 0 , f = 1 MHz	C _T	3	pF
Reverse Recovery Time at I _F = 10 mA	t _{rr}	4	ns

Typical Characteristics

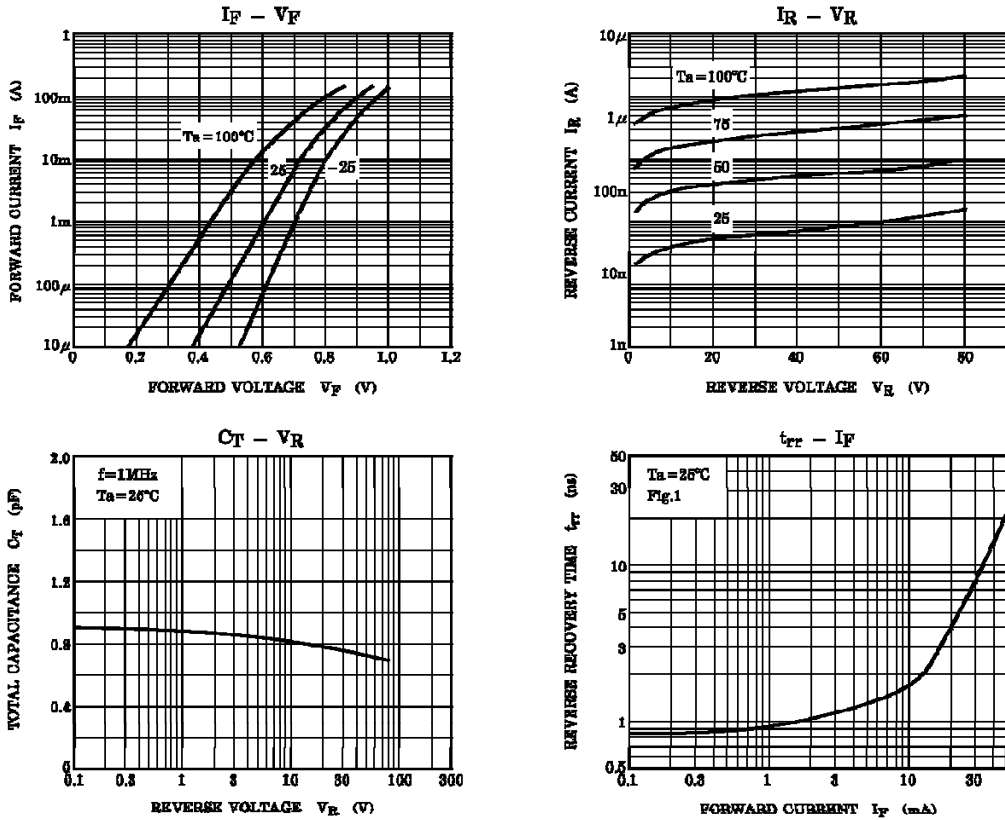
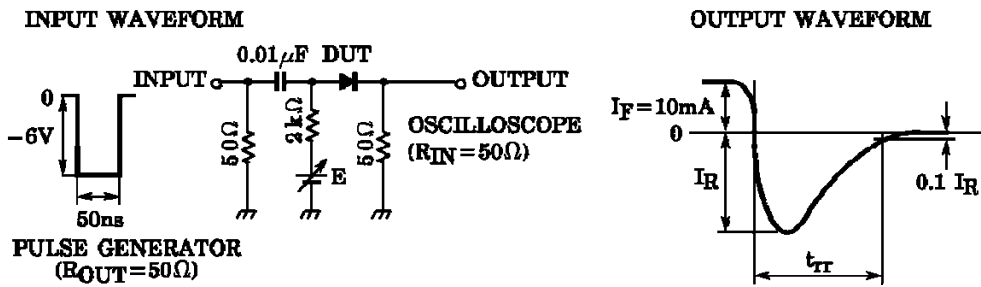


Fig.1 Reverse recovery time (t_{rr}) test circuit





Package Dimensions

SOT-23

unit:mm

